

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1526-08** is a Common Base Device Designed for IFF, DME, and Tacan Pulse Applications.

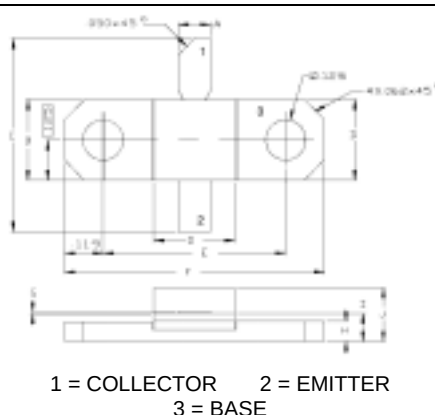
FEATURES INCLUDE:

- Gold Metalization
- Input Matching
- Low Thermal Resistance

MAXIMUM RATINGS

I_C	1.0 A
V_{CES}	45 V
P_{DISS}	21.9 W @ $T_C = 25^\circ\text{C}$
T_J	-55°C to $+200^\circ\text{C}$
T_{STG}	-55°C to $+150^\circ\text{C}$
θ_{JC}	8.0 $^\circ\text{C/W}$

PACKAGE STYLE 250 2L FLG (A)		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.095/.2,41	.105/.2,67
B	.245/.6,22	.255/.6,48
C	.750/.19,05	
D	.245/.6,22	.258/.6,55
E	.555/.14,10	.570/.14,48
F	.795/.20,19	.805/.20,45
G	.003/.0,08	.007/.0,18
H	.055/.1,40	.065/.1,65
I	.075/.1,91	.100/.2,54
J	.150/.3,81	.180/.4,57



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0\text{ mA}$	45			V
BV_{CEO}	$I_C = 5.0\text{ mA}$	45			V
BV_{CES}	$I_C = 5.0\text{ mA}$	45			V
BV_{EBO}	$I_E = 1.0\text{ mA}$	3.5			V
I_{CES}	$V_{CE} = 28\text{ V}$			1.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$	10		200	---
P_G	$V_{CE} = 28\text{ V}$ $P_{out} = 5.0\text{ W}$ $f = 1025\text{ to }1150\text{ MHz}$ PULSE WIDTH = 10 μS DUTY CYCLE = 1.0%	9.5			dB